

external power terminal 61, through an Al bonding wire of, for example, 200 to 500 $\mu\text{m}\phi$, extending from both chips. On the other hand, the surface Cu pattern 63 is connected to an external power terminal 62. Such structure is placed on a heat radiation plate 69. In FIG. 9A, a gate terminal 70 shown in FIG. 9B is not illustrated.

IN THE CLAIMS

Please amend Claims 1 and 11 to read as follows:²

1. (Thrice Amended) A semiconductor device comprising:

at least three power terminals provided one above the other; and

at least one semiconductor chip having a top surface and a bottom surface and

interposed between a predetermined two power terminals of said at least three power terminals in a direction intersecting the top surface and the bottom surface, with the top and bottom surfaces of the at least one semiconductor chip electrically connected to the two power terminals.

11. (Amended) A semiconductor device comprising:

at least three power terminals provided one above another; and

at least one semiconductor chip having a top surface and a bottom surface and

interposed between a predetermined two power terminals of said at least three power terminals in a direction intersecting the top surface and the bottom surface, with the top and bottom surfaces of the at least one semiconductor chip electrically connected to the two power terminals,

wherein one face of said at least one semiconductor chip interposed between said two power terminals is connected to one power terminal of said two power terminals by soldering

²A marked-up copy of the changes made to these claims is attached.